

RJH60D2DPE

Silicon N Channel IGBT Application: Inverter

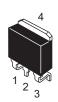
REJ03G1842-0100 Rev.1.00 Oct 14, 2009

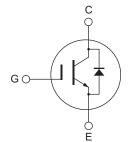
Features

- High breakdown-voltage
- Low on-voltage
- Built-in diode

Outline

RENESAS Package code: PRSS0004AE-B (Package name: LDPAK (S)-(1))





- 1. Gate
- 2. Collector
- 3. Emitter
- 4. Collecotor

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

	Item	Symbol	Ratings	Unit
Collector to emitter voltage / diode reverse voltage		V _{CES} / V _R	600	V
Gate to emitter voltage		V_{GES}	±30	V
Collector current	Tc = 25°C	Ic	20	Α
	Tc = 100°C	Ic	10	Α
Collector peak current		ic(peak) Note1	40	А
Collector to emitter diode forward current		İ _{DF}	10	Α
Collector to emitter diode forward peak current		i _D (peak) Note1	40	Α
Collector dissipation		P _C Note2	90	W
Junction to case thermal impedance		θj-c ^{Note2}	1.39	°C/W
Junction temperature		Tj	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

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Electrical Characteristics

 $(Ta = 25^{\circ}C)$

ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current	I _{CES} / I _R	_	_	100	μΑ	V _{CE} = 600 V, V _{GE} = 0
/ diode reverse current						
Gate to emitter leak current	I _{GES}	_	_	±1	μΑ	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	4.0	_	6.0	V	V _{CE} = 10 V, I _C = 1 mA
Collector to emitter saturation voltage	V _{CE(sat}	_	1.6	2.2	V	I _C = 10 A, V _{GE} = 15 V Note3
	V _{CE(sat}	_	1.8	_	V	I _C = 20 A, V _{GE} = 15 V Note3
Input capacitance	Cies	_	430	_	pF	V _{CE} = 25 V
Output capacitance	Coes	_	35	_	pF	V _{GE} = 0
Reveres transfer capacitance	Cres	_	15	_	pF	f = 1 MHz
Total gate charge	Qg	_	19.1	_	nC	V _{GE} = 15 V
Gate to emitter charge	Qge	_	3.0	_	nC	V _{CE} = 300 V
Gate to collector charge	Qgc	_	9.0	_	nC	I _C = 10 A
Switching time	t _{d(on)}	_	30	_	ns	I _C = 10 A
	t _r	_	30	_	ns	$R_L = 30.0 \Omega$
	t _{d(off)}	_	50	_	ns	V _{GE} = 15 V
	t _f	_	90	_	ns	$Rg = 5 \Omega$
FRD forward voltage	V _F	_	1.8	2.3	V	I _F = 10 A ^{Note3}

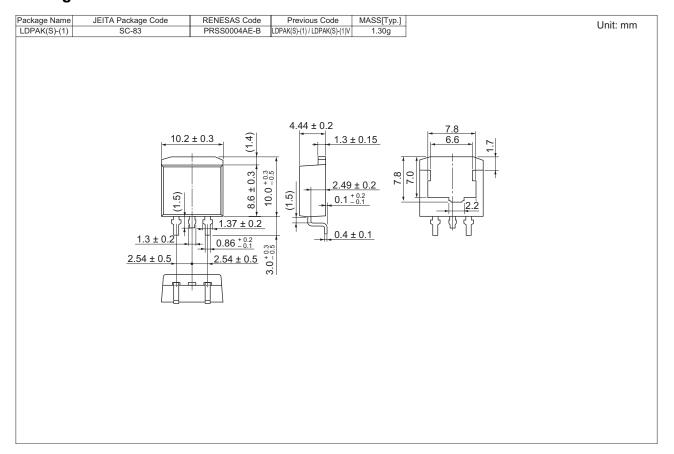
FRD forward voltage	V_{F}	_	1.8	2.3	V	I _F = 10 A ^{Note3}
FRD reverse recovery time	t _{rr}	_	100	_	ns	I _F = 10 A
						di _F /dt = 100 A/μs

Notes: 3. Pulse test.

4. Under development — The specifications potentially be changed without notice.

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Package Dimension



Ordering Information

Part No.	Quantity	Shipping Container
RJH60D2DPE-00-J3	1000 pcs	Taping

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